

CLAIMS:

1. A method of measuring alignment of a substrate, provided with at least one substrate alignment mark having a periodic structure, with respect to a reference alignment mark having a periodic structure, prior to imaging a mask pattern in a resist layer on the substrate, which method comprises the steps of:

5 - illuminating a substrate alignment mark with an alignment beam and imaging this mark on a reference alignment mark, and
- determining the intensity of alignment radiation from the reference alignment mark,

characterized by the steps of:

10 - using a substrate alignment mark having a periodic structure with a period p_1 which is substantially smaller than the period of the reference alignment mark;
- providing the resist layer with an additional alignment mark having a periodic structure with a period p_2 such that, upon illumination by the alignment beam of the substrate alignment mark and the additional alignment mark, an interference pattern is generated
15 having a period which is substantially equal to the period of the reference alignment mark, and
- imaging the interference pattern on the reference alignment mark.

2. A method as claimed in claim 1 characterized in that use is made of a substrate
20 reference alignment mark having substantially the same period as the interference pattern, the substrate reference alignment mark is imaged on the reference alignment mark, and the difference between the positions of the image of the interference pattern and that of the substrate reference alignment mark with respect to the reference alignment mark is determined.

25 3. A method as claimed in claim 1 or 2, characterized in that use is made of gratings for the substrate alignment mark, the additional alignment mark and the reference alignment mark.

4. A method as claimed in claim 1, 2, or 3, characterized in that the additional alignment mark is a latent mark.

5. A method of aligning a substrate with respect to a mask, using a global alignment-measuring method of measuring the position of a global substrate alignment mark with respect to a global reference alignment mark, which method is characterized by the steps of:

- providing a substrate with a substrate reference alignment mark and a substrate fine alignment mark having a period which is substantially smaller than that of the substrate reference alignment mark, which substrate is covered with a resist layer;
- aligning the substrate reference alignment mark with respect to a non-substrate reference alignment mark, using a coarse-alignment-measuring method;
- providing the resist layer with an additional alignment mark having a period of the same order as that of the substrate fine alignment mark;
- measuring the alignment of the substrate fine alignment mark with respect to the additional alignment mark by illuminating these two marks and imaging the resulting interference pattern on the non-substrate reference alignment mark, and
- using the measuring signal of this measurement to correct the signal obtained with the coarse alignment method.

6. A method as claimed in any one of claims 1 to 5, characterized in that it is based on the on-axis alignment principle.

7. A method as claimed in claim 6, characterized in that the interference pattern is imaged on a mask alignment mark via an optical filter, which selects diffraction orders of the radiation from the substrate alignment marks to proceed to said mask alignment mark.

8. A method as claimed in any one of claims 1 to 5, characterized in that it is based on the off-axis alignment principle.

9. A method of manufacturing devices in at least one layer of a substrate, which method comprises at least one set of the following successive steps:

- aligning a mask provided with a mask pattern comprising pattern features corresponding to a device feature to be configured in said layer;

- imaging, by means of projection radiation, the mask pattern in a radiation-sensitive layer on the substrate, and

- removing material from, or adding material to, areas of said layer and substrate, which areas are delineated by the mask pattern image, characterized in that the

5 alignment is carried out by means of the alignment-measuring method as claimed in any one of claims 1 to 8.

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